

CD4011B, CD4012B, CD4023B Types

CMOS NAND GATES

High-Voltage Types (20-Volt Rating)

- Quad 2 Input – CD4011B
- Dual 4 Input – CD4012B
- Triple 3 Input – CD4023B

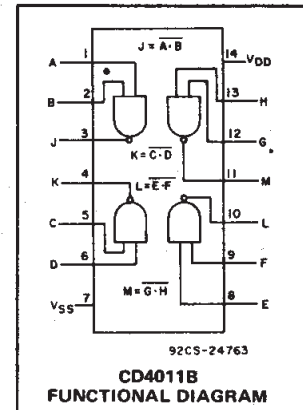
■ CD4011B, CD4012B, and CD4023B NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of CMOS gates. All inputs and outputs are buffered.

The CD4011B, CD4012B, and CD4023B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

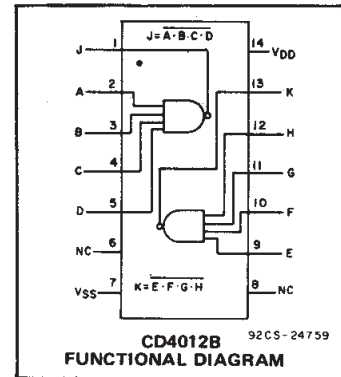
- Propagation delay time = 60 ns (typ.) at $C_L = 50$ pF, $V_{DD} = 10$ V
- Buffered inputs and outputs
- Standardized symmetrical output characteristics
- Maximum input current of $1 \mu A$ at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Noise margin (over full package temperature range):
 - 1 V at $V_{DD} = 5$ V
 - 2 V at $V_{DD} = 10$ V
 - 2.5 V at $V_{DD} = 15$ V

- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of "B" Series CMOS Devices"



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})		
Voltages referenced to V_{SS} Terminal		-0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS		-0.5V to $V_{DD} + 0.5V$
DC INPUT CURRENT, ANY ONE INPUT		± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):		
For $T_A = -55^\circ C$ to $+100^\circ C$		500 mW
For $T_A = +100^\circ C$ to $+125^\circ C$	Derate Linearly at 12mW/°C to 200mW	
DEVICE DISSIPATION PER OUTPUT TRANSISTOR		
FOR $T_A =$ FULL PACKAGE-TEMPERATURE RANGE (All Package Types)		100 mW
OPERATING-TEMPERATURE RANGE (T_A)		$-55^\circ C$ to $+125^\circ C$
STORAGE TEMPERATURE RANGE (T_{stg})		$-65^\circ C$ to $+150^\circ C$
LEAD TEMPERATURE (DURING SOLDERING):		
At distance $1/16 \pm 1/32$ inch (1.59 ± 0.79 mm) from case for 10s max		$+265^\circ C$

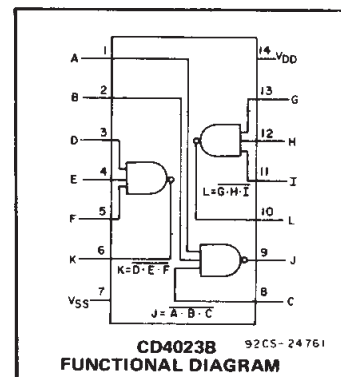
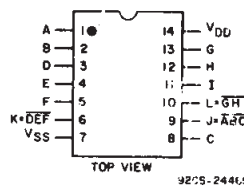
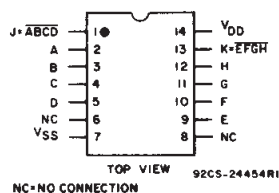
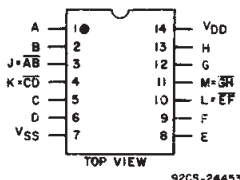


RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For $T_A =$ Full Package Temperature Range)	3	18	V

TERMINAL ASSIGNMENTS



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STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55			+25			Max.	
				Min.	Typ.	Max.	Min.	Typ.	Max.		
Quiescent Device Current, I _{DD} Max.	-	0,5	5	0.25	0.25	7.5	7.5	-	0.01	0.25	μA
	-	0,10	10	0.5	0.5	15	15	-	0.01	0.5	
	-	0,15	15	1	1	30	30	-	0.01	1	
	-	0,20	20	5	5	150	150	-	0.02	5	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage: Low-Level, V _{OL} Max.	-	0,5	5	0.05			0			0.05	V
	-	0,10	10	0.05			0			0.05	
	-	0,15	15	0.05			0			0.05	
Output Voltage: High-Level, V _{OH} Min.	-	0,5	5	4.95			4.95			5	V
	-	0,10	10	9.95			9.95			10	
	-	0,15	15	14.95			14.95			15	
Input Low Voltage, V _{IL} Max.	4.5	-	5	1.5			-			1.5	V
	9	-	10	3			-			3	
	13.5	-	15	4			-			4	
Input High Voltage, V _{IH} Min.	0.5, 4.5	-	5	3.5			3.5			-	V
	1, 9	-	10	7			7			-	
Input Current I _{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μA

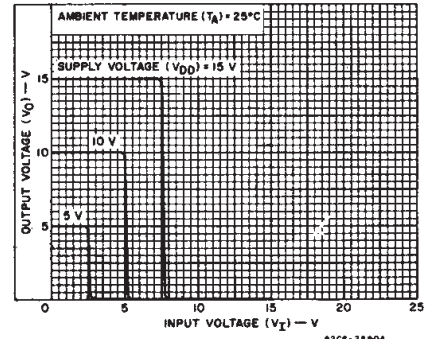


Fig. 1 - Typical voltage transfer characteristics.

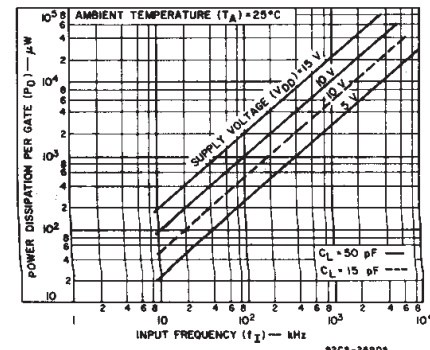


Fig. 2 - Typical power dissipation characteristics.

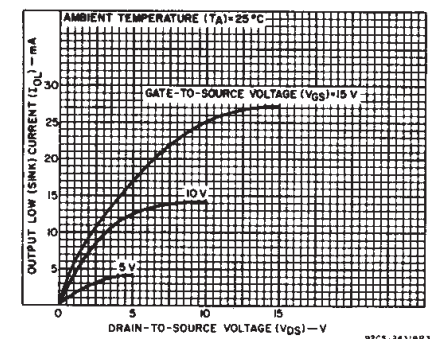


Fig. 3 - Typical output low (sink) current characteristics.

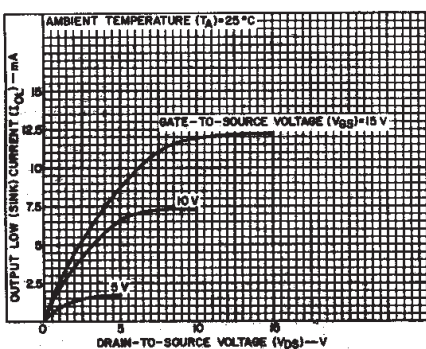


Fig. 4 - Minimum output low (sink) current characteristics.

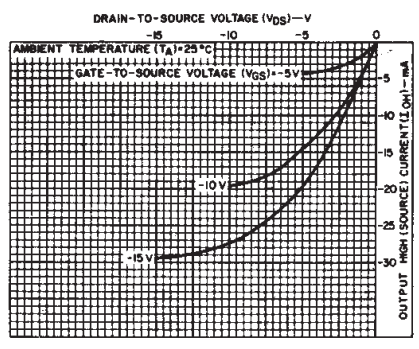


Fig. 5 - Typical output high (source) current characteristics.

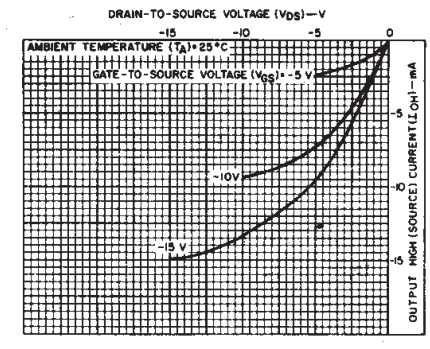
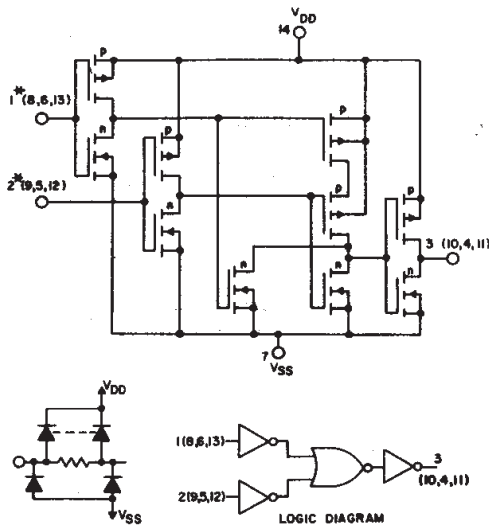


Fig. 6 - Minimum output high (source) current characteristics.

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HIGH VOLTAGE ICs

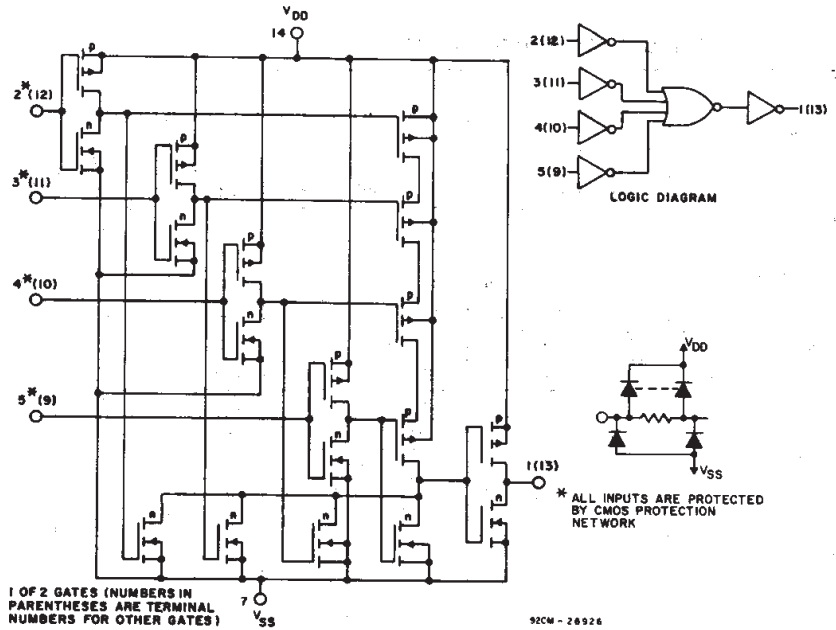
CD4011B, CD4012B, CD4023B Types



* ALL INPUTS ARE PROTECTED BY CMOS PROTECTION NETWORK

1 OF 4 GATES (NUMBERS IN PARENTHESES ARE TERMINAL NUMBERS FOR OTHER GATES)

Fig.7 - Schematic and logic diagrams for CD4011B.



1 OF 2 GATES (NUMBERS IN PARENTHESES ARE TERMINAL NUMBERS FOR OTHER GATES)

Fig.8 - Schematic and logic diagrams for CD4012B.

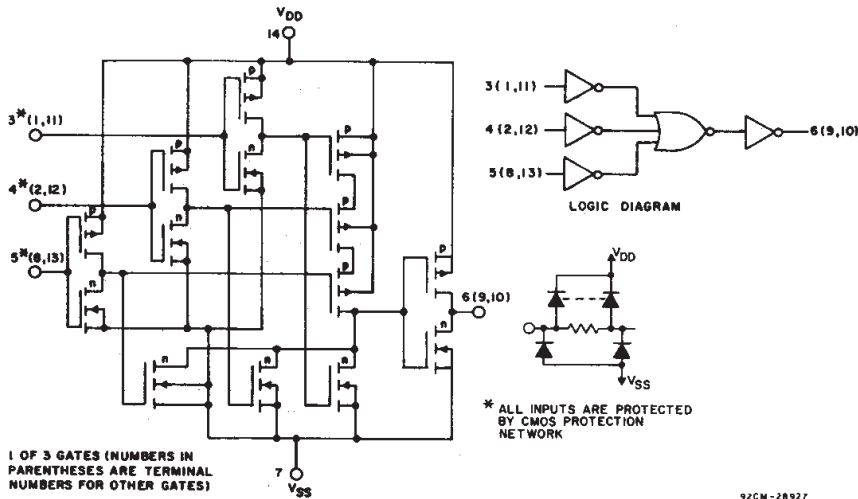


Fig. 9 - Schematic and logic diagrams for CD4023B.

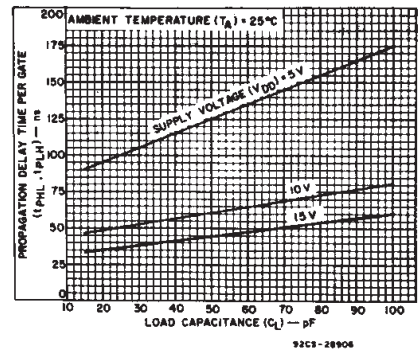


Fig.10 - Typical propagation delay time per gate as a function of load capacitance.

DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	TEST CONDITIONS	LIMITS		UNITS	
		V _{DD} VOLTS	TYP.		MAX.
Propagation Delay Time, t _{PHL} , t _{PLH}		5	125	250	ns
		10	60	120	
		15	45	90	
Transition Time, t _{THL} , t _{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C _{IN}	Any Input		5	7.5	pF

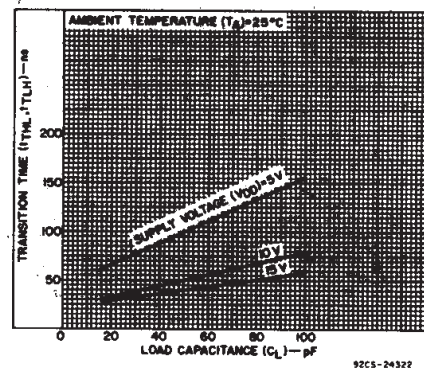


Fig.11 - Typical transition time as a function of load capacitance.

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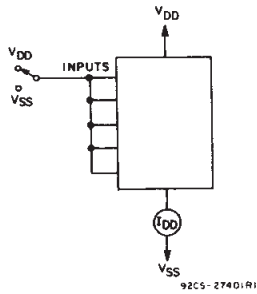


Fig. 12 - Quiescent-device-current test circuit.

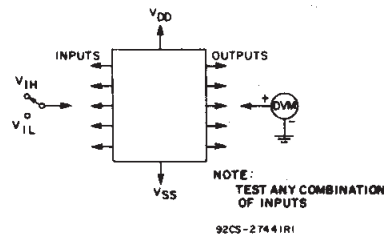


Fig. 13 - Input-voltage test circuit.

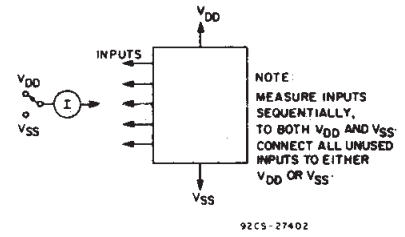
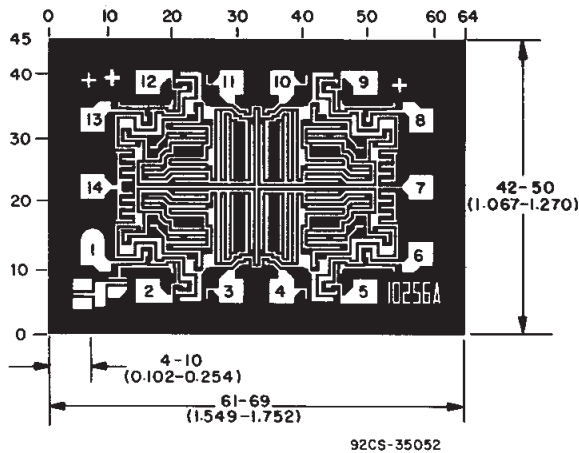
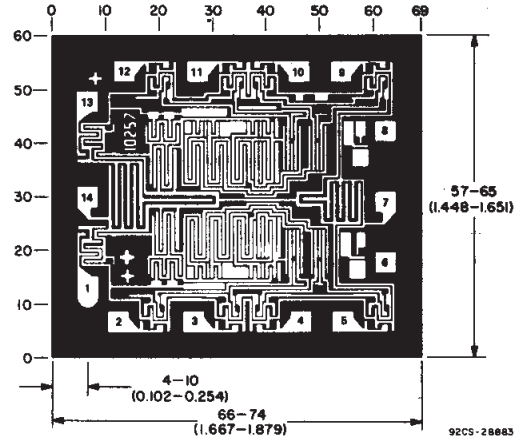


Fig. 14 - Input-current test circuit.

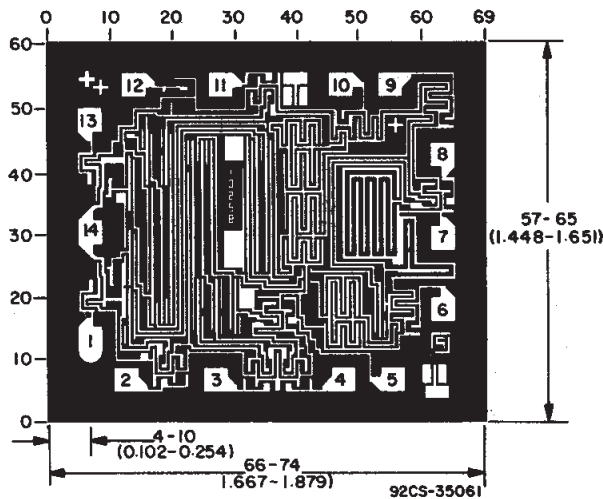
Chip Dimensions and Pad Layouts



CD4011BH



CD4012BH



CD4023BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

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